

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1842	((438/199) or (438/207) or (438/222) or (438/483)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/13 20:10
L2	6554	(si silicon) near2 (germanium ge) near2 (carbon c!) sigec sicge csige cgesi gesic gecsi	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 20:11
L3	764178	mask\$4 photoresist pr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 20:11
L4	234889	mosfet or (metal adj (oxide or insulat\$4) adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 20:11
L5	5130418	aperture opening gap hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 20:11
L6	1	(L3 with L5 and L2 and L4).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 20:17
S12 3	6488	(si silicon) near2 (germanium ge) near2 (carbon c!) sigec sicge csige cgesi gesic gecsi	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 20:25
S12 4	760290	mask\$4 photoresist pr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 20:25
S12 5	233299	mosfet or (metal adj (oxide or insulat\$4) adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 20:27

S12 6	5114873	aperture opening gap hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 20:27
S12 7	0	S124 near4 S126 near4 S123 and S125	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 20:28
S12 8	5	S124 with S126 with S123 and S125	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 20:30
S12 9	4	S128 and (@ad < "20021202")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 20:30
S13 0	343	S124 with S126 and S123 and S125	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 20:31
S13 1	197	S130 and (@ad < "20021202")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/03 19:37
S13 2	10	S124 with S126 same S123 and S125	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/22 20:31
S13 3	6	S132 and (@ad < "20021202")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/03 19:20
S13 4	6514	(si silicon) near2 (germanium ge) near2 (carbon c!) sigec sicge csige cgesi gesic gecsi	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/03 19:20
S13 5	762131	mask\$4 photoresist pr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/03 19:20

S13 6	234080	mosfet or (metal adj (oxide or insulat\$4) adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/03 19:20
S13 7	5122917	perature opening gap hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/03 19:20
S13 8	10	S135 with S137 same S134 and S136	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/03 19:20
S13 9	6	S138 and (@ad < "20021202")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/03 19:22
S14 0	345	S135 with S137 and S134 and S136	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/13 20:11
S14 1	197	S140 and (@ad < "20021202")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/03 19:38